

<b>SANYO</b>	No.1287C	<h1 style="margin: 0;">2SA1345/2SC3399</h1> <p style="margin: 0;">PNP/NPN Epitaxial Planar Silicon Transistors</p> <h2 style="margin: 0;">Switching Applications</h2> <p style="margin: 0;">(with Bias Resistance)</p>
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**Applications**

Switching circuit, inverter, interface circuit, driver

**Features**

- Built-in bias resistor ( $R_1=47k\Omega$ ,  $R_2=47k\Omega$ ).
- Small-sized package (SPA).

( ): 2SA1345

**Absolute Maximum Ratings/ $T_a=25^\circ\text{C}$**

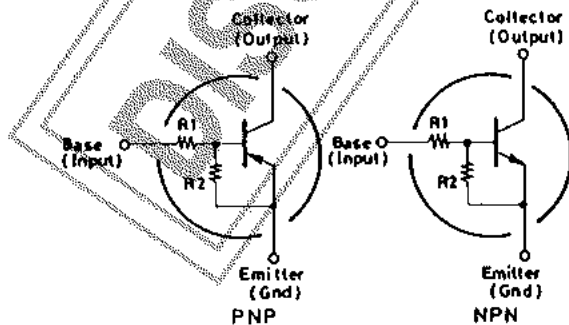
			unit
Collector to Base Voltage	$V_{CBO}$	(-150)	V
Collector to Emitter Voltage	$V_{CEO}$	(-150)	V
Emitter to Base Voltage	$V_{EBO}$	(-10)	V
Collector Current	$I_C$	(-100)	mA
Collector Current(Pulse)	$I_{CP}$	(-200)	mA
Collector Dissipation	$P_C$	300	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

**Electrical Characteristics/ $T_a=25^\circ\text{C}$**

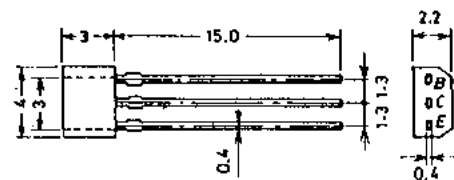
			min	typ	max	unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = (-140\text{V}, I_E = 0$			(-)0.1	$\mu\text{A}$
Collector Cutoff Current	$I_{CEO}$	$V_{CE} = (-140\text{V}, I_B = 0$			(-)0.5	$\mu\text{A}$
Emitter Cutoff Current	$I_{EBO}$	$V_{EB} = (-15\text{V}, I_C = 0$	(-)30	(-)53	(-)80	$\mu\text{A}$
DC Current Gain	$h_{FE}$	$V_{CE} = (-15\text{V}, I_C = (-)5\text{mA}$	50			
Gain-bandwidth product	$f_T$	$V_{CE} = (-)10\text{V}, I_C = (-)5\text{mA}$		250 (200)		MHz
Output Capacitance	$c_{ob}$	$V_{CB} = (-)10\text{V}, f = 1\text{MHz}$		3.7 (5.5)		pF
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = (-)5\text{mA}, I_B = (-)0.25\text{mA}$	(-)0.1	(-)0.3		V

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**Electrical Connection**



**Case Outline 2033 (unit: mm)**



B: Base  
C: Collector  
E: Emitter  
SANYO: SPA

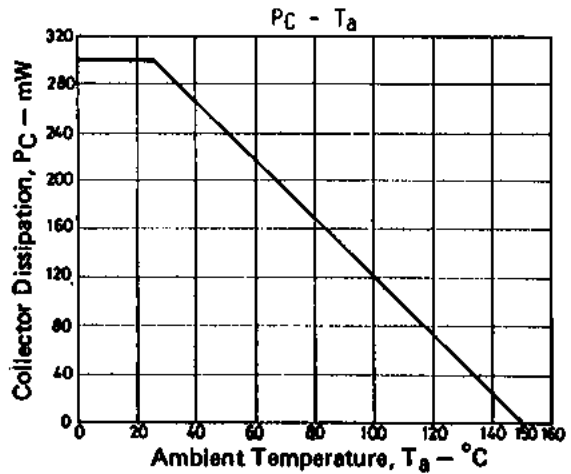
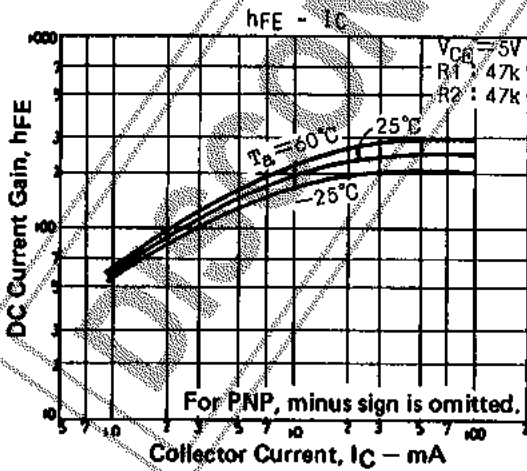
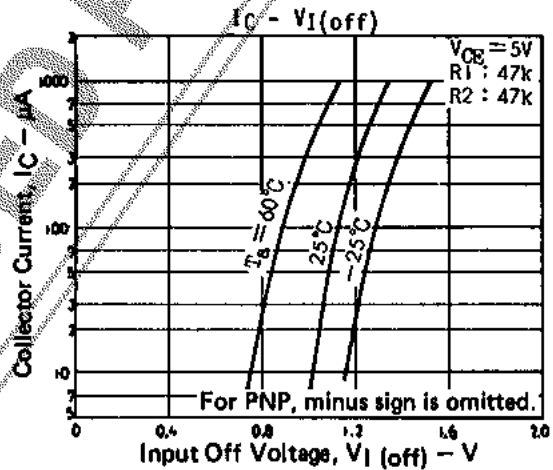
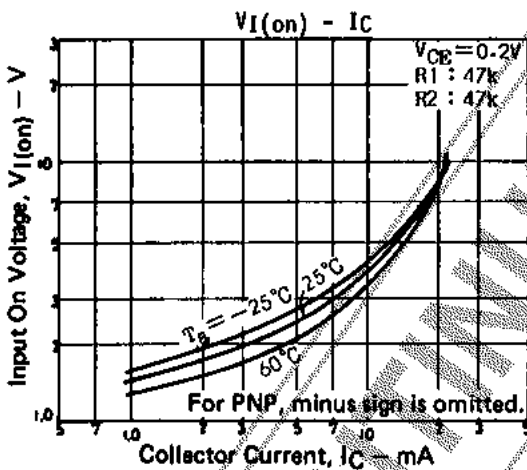
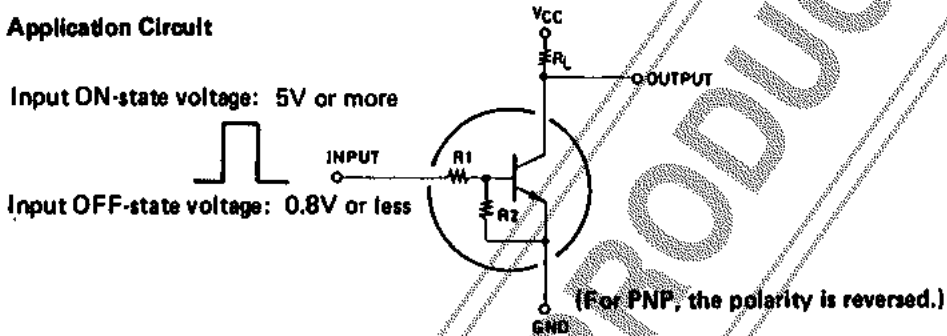
Specifications and information herein are subject to change without notice.

**SANYO Electric Co., Ltd. Semiconductor Business Headquarters**  
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taitu-ku, TOKYO, 110 JAPAN

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			min	typ	max	unit
Collector to Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=(-)10\mu A, I_E=0$	(-)50			V
Collector to Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=(-)100\mu A, R_{BE}=\infty$	(-)50			V
Input Off Voltage	$V_{I(off)}$	$V_{CE}=(-)5V, I_C=(-)100\mu A$	(-)0.8	(-)1.1	(-)1.5	V
Input On Voltage	$V_{I(on)}$	$V_{CE}=(-)0.2V, I_C=(-)5mA$	(-)1.0	(-)2.5	(-)5.0	V
Input Resistance	$R_1$		32	47	62	k $\Omega$
Input Resistance Ratio	$R_1/R_2$		0.9	1.0	1.1	

■ Sample Application Circuit



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[www.DatasheetCatalog.com](http://www.DatasheetCatalog.com)

Datasheets for electronic components.